

Kun Ren

List of Publications by Year in descending order

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24
papers

660
citations

623734

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642732

23
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all docs

24
docs citations

24
times ranked

502
citing authors

#	ARTICLE	IF	CITATIONS
1	Position selective dielectric polarization enhancement in CNT based heterostructures for highly efficient microwave absorption. <i>Nanoscale</i> , 2021, 13, 2324-2332.	5.6	30
2	Logical devices based on the antiferromagnetic-antimeron in a ferromagnet nanodot with gain. <i>Applied Physics Letters</i> , 2021, 118, 172410.	3.3	3
3	Mineralogical phase separation and leaching characteristics of typical toxic elements in Chinese lignite fly ash. <i>Science of the Total Environment</i> , 2020, 708, 135095.	8.0	22
4	Crystal-Like Glassy Structure in Sc-Doped BiSbTe Ensuring Excellent Speed and Power Efficiency in Phase Change Memory. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 16601-16608.	8.0	11
5	Constructing reliable PCM and OTS devices with an interfacial carbon layer. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 20037-20042.	2.2	7
6	Reducing structural change in the phase transition of Ge-doped Bi _{0.5} Sb _{1.5} Te ₃ to enable high-speed and low-energy memory switching. <i>Journal of Materials Chemistry C</i> , 2019, 7, 11813-11823.	5.5	10
7	Ovonic threshold switching selectors for three-dimensional stackable phase-change memory. <i>MRS Bulletin</i> , 2019, 44, 715-720.	3.5	70
8	Electrical switching properties and structural characteristics of GeSe/GeTe films. <i>Nanoscale</i> , 2019, 11, 1595-1603.	5.6	30
9	High thermal stability and fast speed phase change memory by optimizing GeSbTe with Scandium doping. <i>Scripta Materialia</i> , 2019, 164, 25-29.	5.2	24
10	In-situ observation of Ge ₂ Sb ₂ Te ₅ crystallization at the passivated interface. <i>Ceramics International</i> , 2019, 45, 19542-19546.	4.8	6
11	Sc-Centered Octahedron Enables High-Speed Phase Change Memory with Improved Data Retention and Reduced Power Consumption. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 10848-10855.	8.0	31
12	Direct observation of partial disorder and zipperlike transition in crystalline phase change materials. <i>Physical Review Materials</i> , 2019, 3, .	2.4	34
13	Controllable SET process in O-Ti-Sb-Te based phase change memory for synaptic application. <i>Applied Physics Letters</i> , 2018, 112, 073106.	3.3	31
14	Study on the phase change behavior of nitrogen doped Bi ₂ Te ₃ films. <i>Journal of Alloys and Compounds</i> , 2018, 754, 227-231.	5.5	9
15	Scandium doped Ge ₂ Sb ₂ Te ₅ for high-speed and low-power-consumption phase change memory. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	45
16	Atomic scale insight into the effects of Aluminum doped Sb ₂ Te for phase change memory application. <i>Scientific Reports</i> , 2018, 8, 15136.	3.3	15
17	Carbon layer application in phase change memory to reduce power consumption and atomic migration. <i>Materials Letters</i> , 2017, 206, 52-55.	2.6	10
18	Uniform Ti-doped Sb ₂ Te ₃ materials for high-speed phase change memory applications. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	77

#	ARTICLE	IF	CITATIONS
19	Study on the thermal stability improvement of GeTe by Al doping. Applied Physics Letters, 2013, 103, .	3.3	14
20	W-Sb-Te phase-change material: A candidate for the trade-off between programming speed and data retention. Applied Physics Letters, 2012, 101, .	3.3	56
21	Ti10Sb60Te30 for phase change memory with high-temperature data retention and rapid crystallization speed. Applied Physics Letters, 2012, 100, .	3.3	69
22	N-doped Sb2Te phase change materials for higher data retention. Journal of Alloys and Compounds, 2011, 509, 10105-10109.	5.5	46
23	Study on the crystallization behaviors of Si2Sb2Tex materials. Scripta Materialia, 2011, 64, 685-688.	5.2	10
24	Defect Engineering in Antimony Telluride Phase-Change Materials. Materials Science Forum, 0, 944, 607-612.	0.3	0